

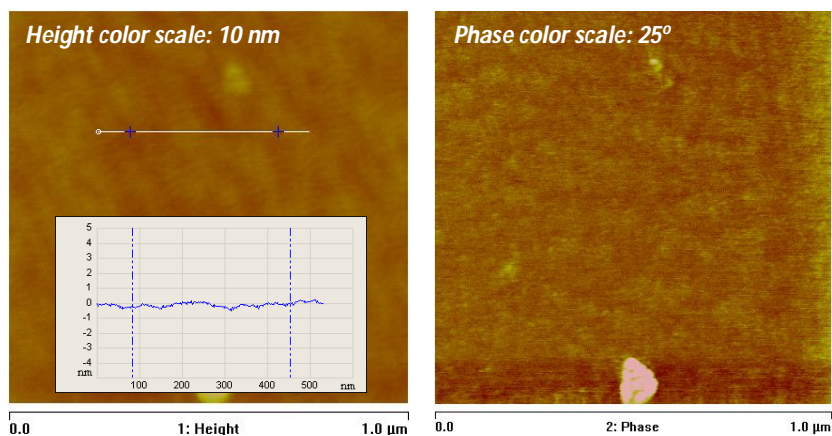
Supporting Information

Resist Free Patterning of Nonpreferential Buffer Layers for Block Copolymer Lithography

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(a) PS-*b*-PMMA-OH ($F_{st}=0.18$)



(b) PS-*b*-PMMA-OH ($F_{st}=0.25$)

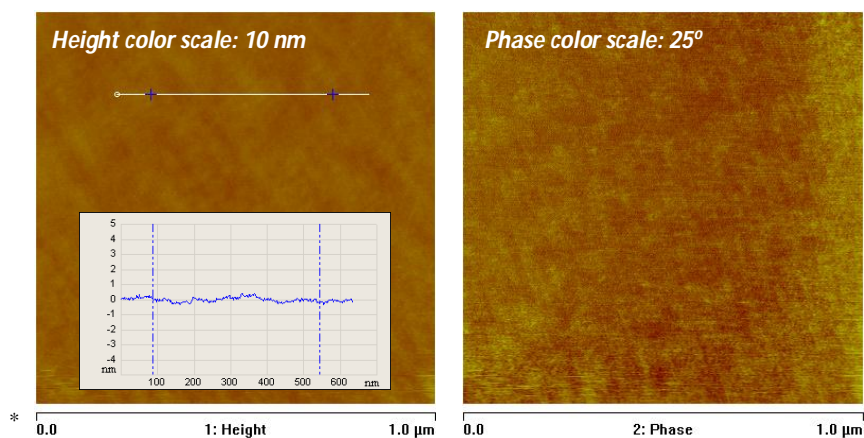


Figure S1. AFM analysis of grafted block copolymers showing smooth surfaces after thermal annealing at 190 °C for 12h.

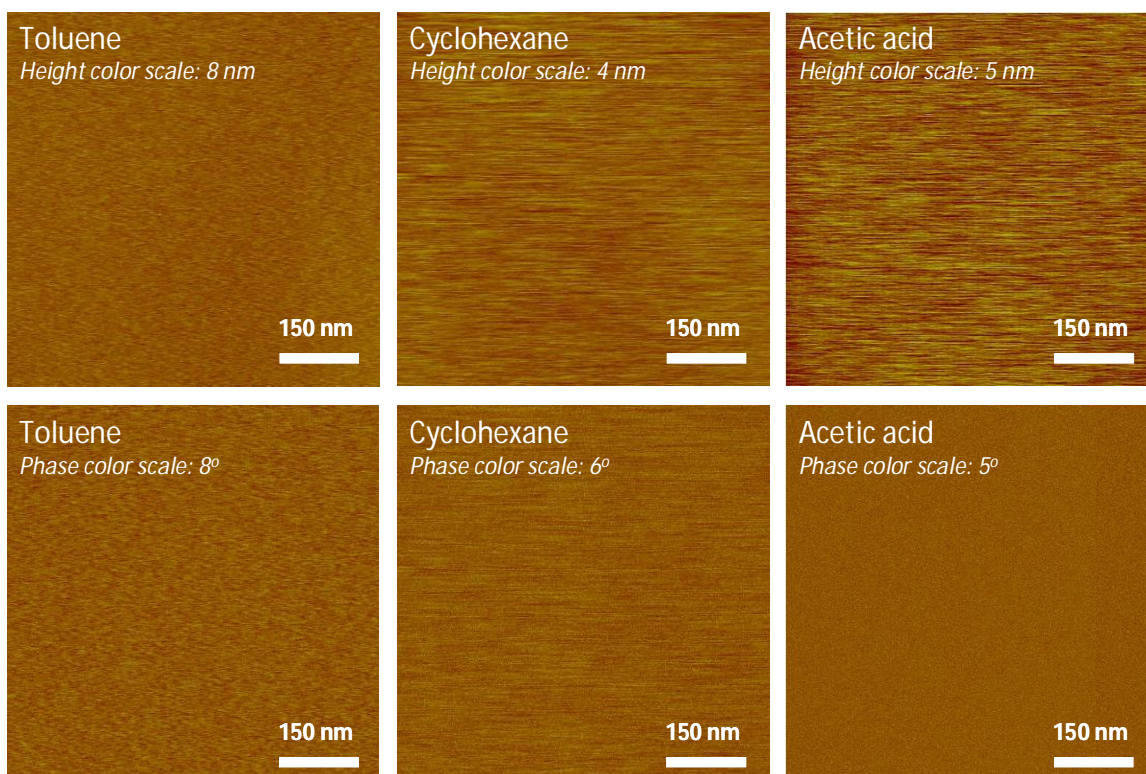


Figure S2. AFM analysis of grafted block copolymer ($F_{St}=0.25$) showing smooth surfaces after various solvent treatment for 30 min.